

Amendments to the Specification

Please amend the paragraph beginning on line 1 of page 13 as follows:

An opening has been formed through insulative material layer 32 to one of the source/drain regions 28, and subsequently filled with a conductive material 34. Conductive material 34 can comprise, for example, a metal and/or a conductively doped silicon. In particular embodiments, conductive material 34 comprises conductively-doped polycrystalline silicon. The polycrystalline silicon can be conductively-doped with either n-type or p-type dopant. ~~Conductively~~ Conductive material 34 ultimately comprises a first electrical node of a capacitor structure. Although conductive material 34 is shown with a planar upper surface, it is to be understood that conductive material 34 can have a roughened surface, such as, for example, a surface of hemispherical grain polysilicon. Also, although conductive material 34 is shown as a plug, it is to be understood that conductive material 34 can have other shapes, such as, for example, a container shape.

Please amend the paragraph beginning on line 1 of page 17 as follows:

Referring to Fig. 3, a conductive material 42 is formed over dielectric material 40. Conductive material 42 can comprise, for example, conductively doped silicon, and/or a metal. In the shown embodiment, conductive material 42 is illustrated as being patterned to have sidewalls coextensive with sidewalls of dielectric material 40. Such can be accomplished by, for example, forming conductive material 42 to extend past sidewalls of dielectric material 40, ~~and then~~ subsequently patterning conductive material 42 with photoresist (not shown) ~~and~~ , followed by an appropriate etch of conductive material 42. In alternative embodiments (not shown), conductive material 42 can be formed to extend beyond sidewalls of dielectric material 40 to define a capacitor plate which extends across several capacitor structures. Conductive material 42 defines a second electrical node which is spaced from first electrical node 34 by dielectric material 40. Accordingly, conductive material 42 is capacitively coupled with conductive material 34 through dielectric material 40; and materials 34, 40 and 42 together define a capacitor structure 44. Dielectric material 40 can be considered to define a dielectric region operatively positioned between electrical nodes 34 and 42 in the capacitor construction 44 of Fig. 4.